MJ10025

NPN Silicon Darlington High Power Transistor

Features:

1. Using triple-diffusion process.High output current. Small driving power.
2. Highest amplification factor. High inverse voltage.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for current output,voltage adjustment and servo circuit of numerical control machine.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	Test Condition
Collector-Emitter Voltage	V_{CEO}	V	850	
Emitter-Base Voltage	V_{EBO}	V	8	
Max. Collector Current	I_{CM}	A	20	
Max. Collector Dissipation	P_{CM}	W	250	T_C:75°C
Junction Temperature	T_{jm}	°C	175	
Storage Temperature	T_{stg}	°C	-55~+175	
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:1.0	V_{CE}=850V
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:2.2	I_C=10A,I_B=1A
DC Current Gain	h_{FE}		Min.:600	V_{CE}=5V,I_C=5A
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	850	I_C=1mA
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	8	I_E=20mA

Outline and Dimensions: